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**INFORMATION DISCLOSURE  
 STATEMENT BY APPLICANT**  
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PTO/SB/06A(10-01)  
 Approved for use through 10/31/2002. OMB 051-0031  
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Complete if Known	
Application Number	Unknown 10/600 965
Filing Date	Even Date Herewith 6/20/03
First Named Inventor	Ahn, Kie
Group Art Unit	Unknown 2813
Examiner Name	Tran, Mai-Huong

Sheet 1 of 2

Attorney Docket No: 303.716US2

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Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
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DATE CONSIDERED

8/30/04

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 \* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached

Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE                  STATEMENT BY APPLICANT</b> (Use as many sheets as necessary)	Complete if Known	
	Application Number	<del>Unknown</del> 10/600 965
	Filing Date	<del>Even Date Here with</del> 6/20/03
	First Named Inventor	Ahn, Kie
	Group Art Unit	<del>Unknown</del> 2813
	Examiner Name	Tran, Mai-Huong
Sheet 2 of 2		Attorney Docket No: 303.716US2

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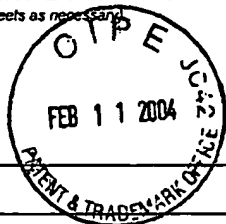
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Application Number	10/600965
Filing Date	June 20, 2003
First Named Inventor	Ahn, Kie
Group Art Unit	2813
Examiner Name	Tran, Mai-Huong

Sheet 1 of 1

Attorney Docket No: 303.716US2

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Substitute Disclosure Statement Form (PTO-1448)

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